优尚

YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Features

- 3.2GHz unity gain for RF switching applications

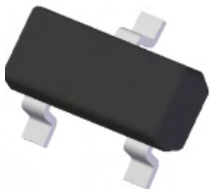
Mechanical Data

- Case: SOT23
- Case material: molded plastic. “Green” molding compound.
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.008 grams (approximate)

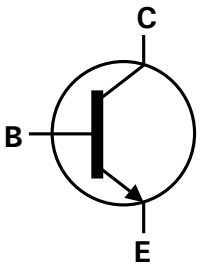
Applications

- RF switch

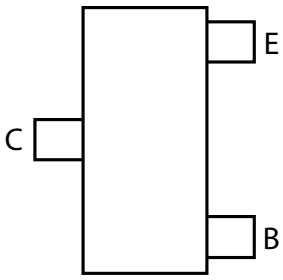
SOT23



Top View



Device symbol



Top View
Pin Out

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	20	V
Collector-Emitter Voltage	V_{CEO}	11	V
Emitter-Base Voltage	V_{EBO}	3	V
Continuous Collector Current	I_C	50	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

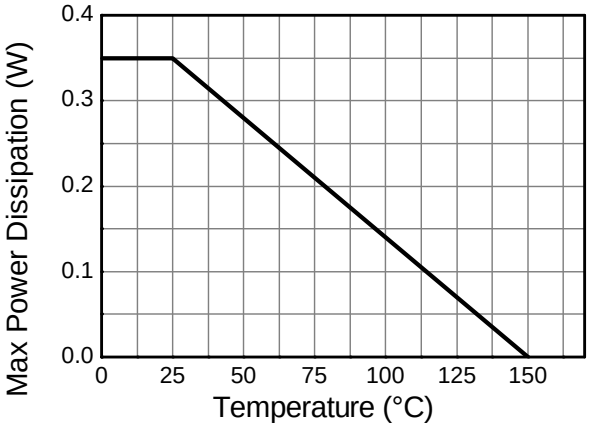
Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 6)	P_D	310	mW
	(Note 7)		350	
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	403	°C/W
	(Note 7)		357	
Thermal Resistance, Junction to Leads	(Note 8)	$R_{\theta JL}$	350	°C/W
Operating and Storage Temperature Range		T_J,T_{STG}	-55 to +150	°C

ESD Ratings (Note 9)

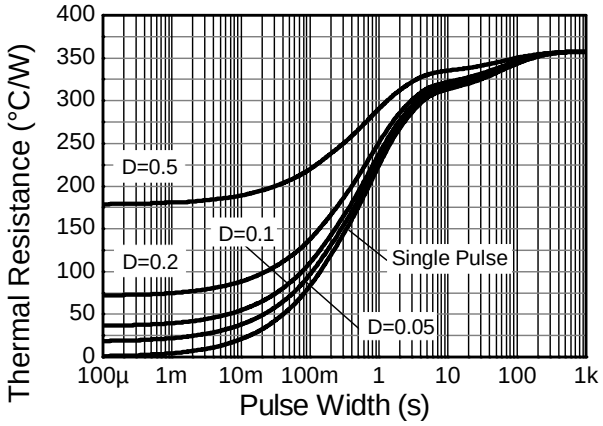
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	2,000	V	2
Electrostatic Discharge - Machine Model	ESD MM	100	V	A

Notes:
6. For the device mounted on minimum recommended pad layout FR4 PCB with high coverage of single sided 1oz copper in still air condition;
7. Same as Note 6, expect the device is mounted on 15mm X 15mm X 1.6mm FR4 PCB
8. Thermal resistance from junction to solder-point (at the end of the leads).
9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

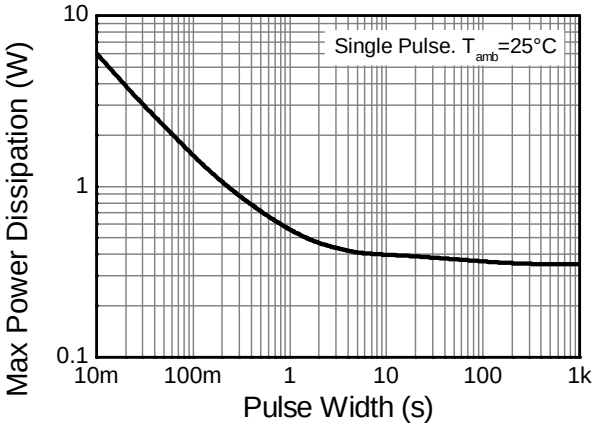
Thermal Characteristics and Derating information



Derating Curve



Transient Thermal Impedance



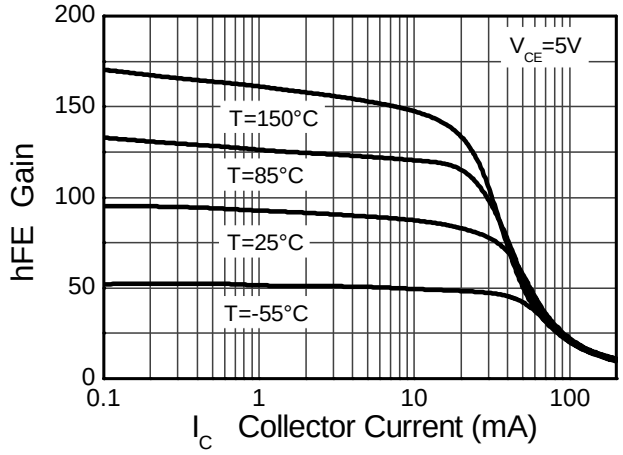
Pulse Power Dissipation

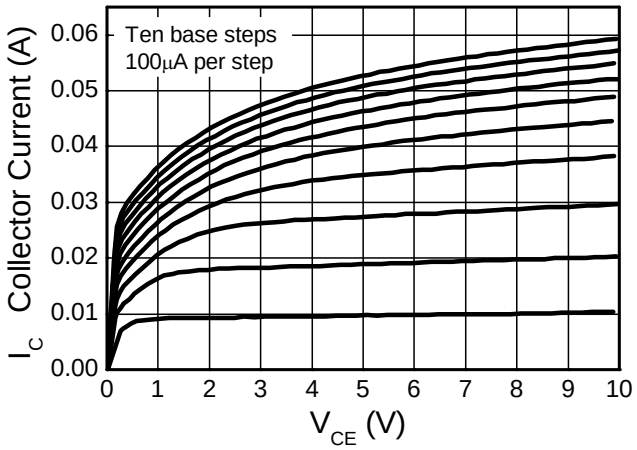
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

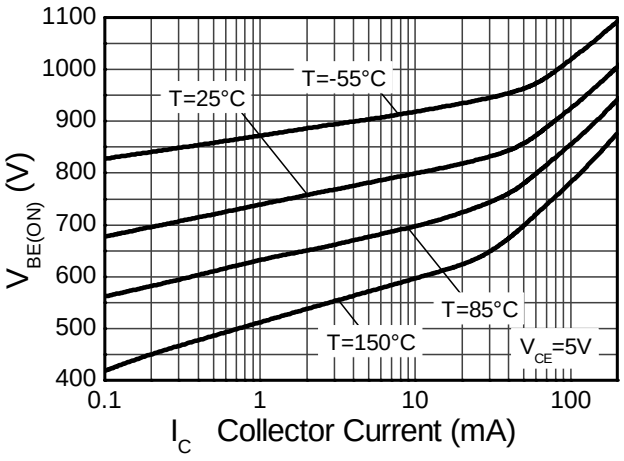
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	20	–	–	V	I_C = 10μA
Collector-Emitter Breakdown Voltage (Note 10)	BV_{CEO}	11	–	–	V	I_C = 1mA
Emitter-Base Breakdown Voltage	BV_{EBO}	3	–	–	V	I_E = 10μA
Collector Cutoff Current	I_{CBO}	–	–	0.5	μA	V_{CB} = 10V
Emitter Cutoff Current	I_{EBO}	–	–	0.5	μA	V_{EB} = 2V
Static Forward Current Transfer Ratio (Note 10)	h_{FE}	56	–	180	–	I_C = 5mA, V_{CE} = 10V
Collector-Emitter Saturation Voltage (Note 10)	$V_{CE(sat)}$	–	–	0.5	V	I_C = 25mA, I_B = 5mA
Transition Frequency (Note 10)	f_T	1.4	3.2	–	GHz	I_E = 25mA, V_{CE} = 5V, f = 500MHz
Collector Output Capacitance (Note 10)	C_{ob}	–	0.8	1.5	pF	V_{CB} = 10V, f = 1MHz

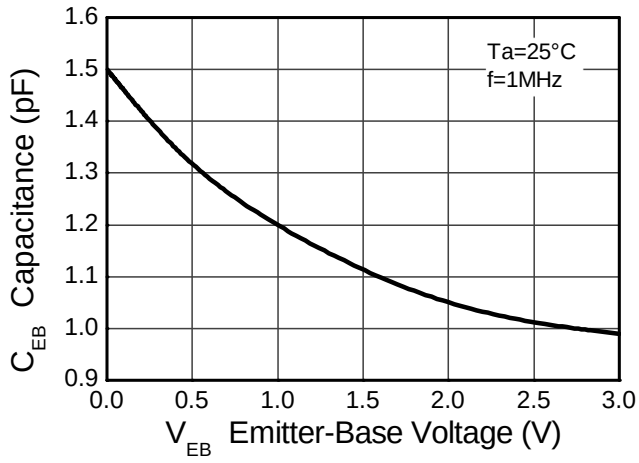
Notes: 10. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%

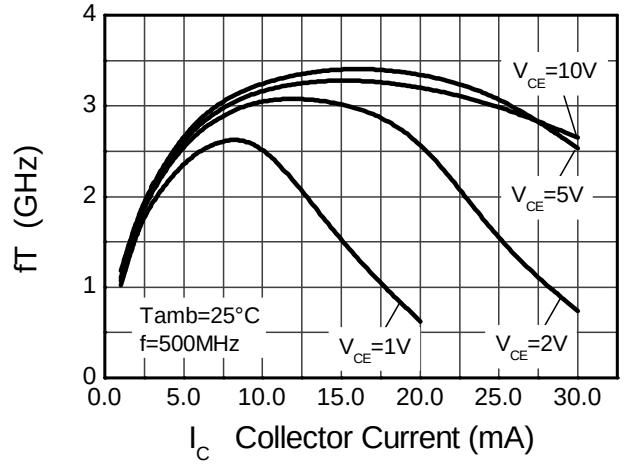
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

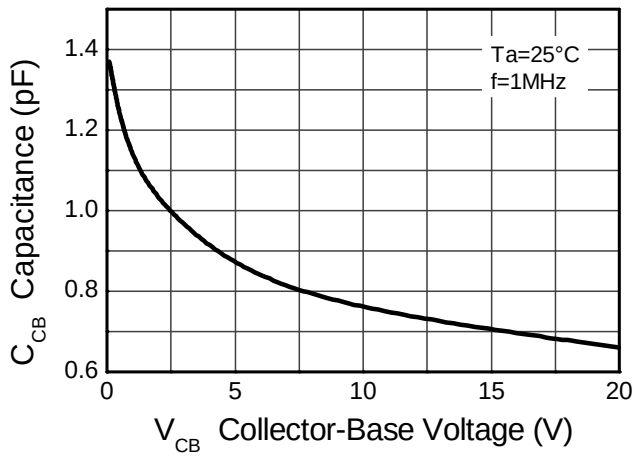




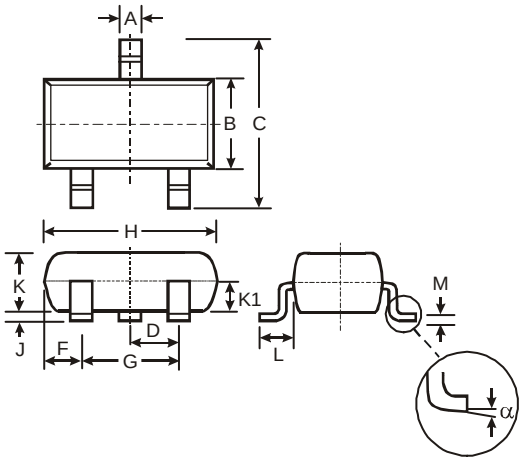






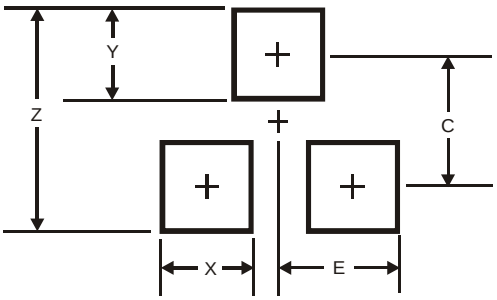


Package Outline Dimensions



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.903	1.10	1.00
K1	-	-	0.400
L	0.45	0.61	0.55
M	0.085	0.18	0.11
α	0°	8°	-
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35